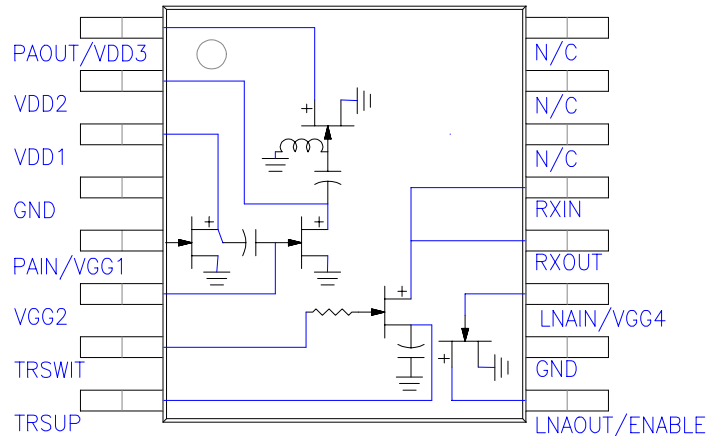


# 3.6V Integrated RF Front-End for DECT ITT2207GF

PRELIMINARY

## FEATURES

- 3.6V Operation
- Single Positive Supply
- 55% Power Added Efficiency
- 100% Duty Cycle
- 1.6 dB LNA Noise Figure
- 16 Pin TSSOP Full Downset Plastic Package
- Self-Aligned MSAG®-Lite MESFET Process



## DESCRIPTION

The ITT2207GF is an integrated DECT front-end based on GaAsTEK's GaAs Self-Aligned MSAG® MESFET Process. This product has an integrated power amplifier, low noise amplifier, and switch in one surface mount package.

## MAXIMUM RATINGS (T<sub>A</sub> = 25 °C unless otherwise noted)

Rating	Symbol	Value	Unit
DC Supply Voltage	V <sub>DD</sub>	+5.5	V
Reverse DC Supply Voltage	-V <sub>DD</sub>	-0.7	V
RF Input Power, P <sub>A<sub>IN</sub></sub>	P <sub>IN</sub>	+10	mW
RF Input Power, LNA <sub>IN</sub>	P <sub>IN</sub>	+10	mW
Junction Temperature	T <sub>J</sub>	+150	°C
Storage Temperature	T <sub>STG</sub>	-40 to +175	°C

## ELECTRICAL CHARACTERISTICS T<sub>s</sub> (Solder Point Temperature) = 40 °C

Characteristic	Symbol	Min	Typ	Max	Unit
Frequency	<i>f</i>	1880	—	1930	MHz
<b>Transmit Path (Power Amplifier + T/R Switch)</b> V <sub>DD1,2,3</sub> = 3.6V, P <sub>IN</sub> =-2 dBm, TR <sub>SUP</sub> =3.6V, TR <sub>SWIT</sub> =3.6V, LNA <sub>ENABLE</sub> =0.0V, <i>f</i> =1900MHz					
Load Power (at Ant)	P <sub>OUT</sub>		25		dBm
Current Consumption	I <sub>DD1,2,3</sub>		226		mA
Input VSWR				2:1	
Harmonics	—		-41		dBc
Duty Cycle	—			100	%
Forward Isolation (RF <sub>IN</sub> to Ant) V <sub>DD1,2,3</sub> =0.0V	—		54		dB
Forward Isolation (ANT to LNA <sub>OUT</sub> )	—		34		dB
<b>Receive Path (T/R Switch + Low Noise Amplifier)</b> V <sub>DD1,2,3</sub> = 0.0V, TR <sub>SUP</sub> =3.6V, TR <sub>SWIT</sub> =0.0V, LNA <sub>ENABLE</sub> =2.4V, <i>f</i> =1900MHz					
Current Consumption	LNA <sub>ENABLE</sub>		4.3		mA
Noise Figure (Ant to LNA <sub>OUT</sub> )	NF		2.1		dB
Gain (Ant to LNA <sub>OUT</sub> )	G		15		dB
Third-Order Input Intercept Point	IIP <sub>3</sub>		3.5		dBm
Reverse Isolation (LNA <sub>OUT</sub> to ANT)	—		18		dB
Thermal Resistance (Junction of 3 <sup>rd</sup> stage FET to solder point of pin 13)	R <sub>th</sub>		37.5		°C/W

Specifications Subject to Change Without Notice

902222 H, December 1999



GaAsTEK  
5310 Valley Park Drive  
Roanoke, VA 24019 USA  
[www.gaastek.com](http://www.gaastek.com)  
Tel: 1-540-563-3949  
1-888-563-3949 (USA)  
Fax: 1-540-563-8616

## TYPICAL CHARACTERISTICS

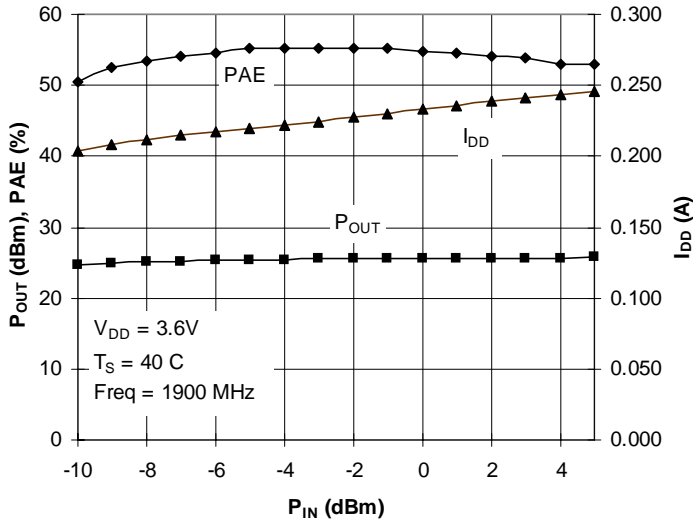


Figure 1. Output power, efficiency and supply current vs. input power

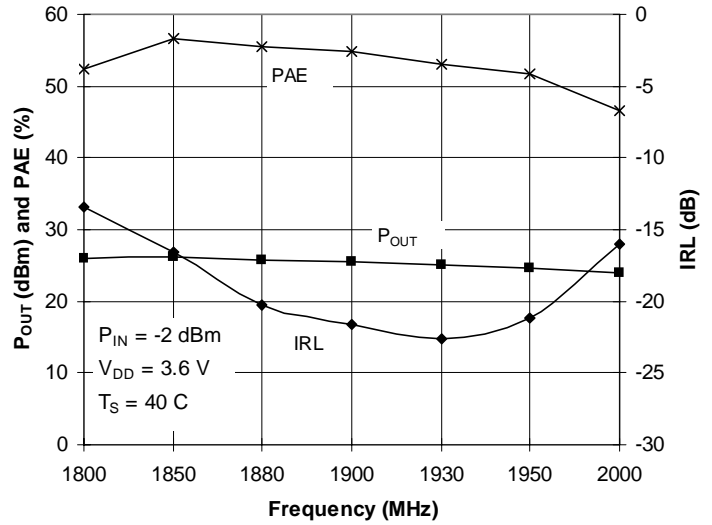


Figure 2. Output power, efficiency and input return loss vs. frequency.

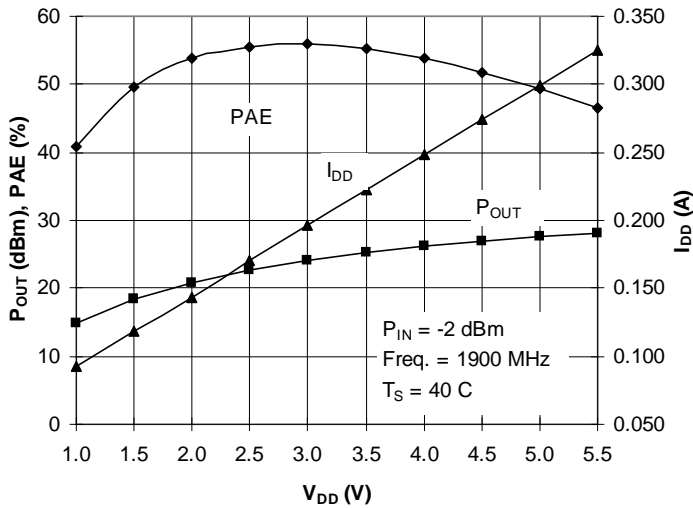


Figure 3. Output power, efficiency and supply current vs. supply voltage

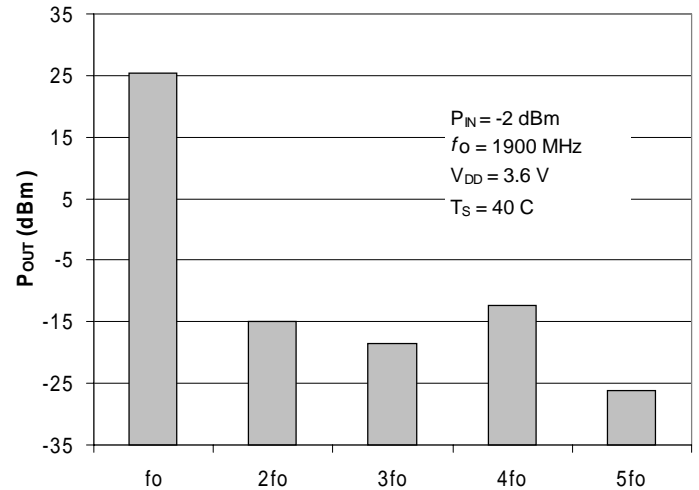


Figure 4. Harmonics

TYPICAL CHARACTERISTICS (CONT)

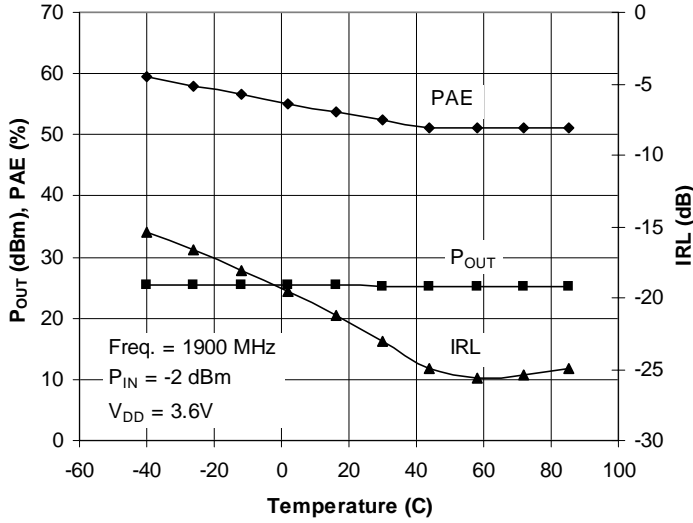


Figure 5. Output power, efficiency and supply current vs. temperature

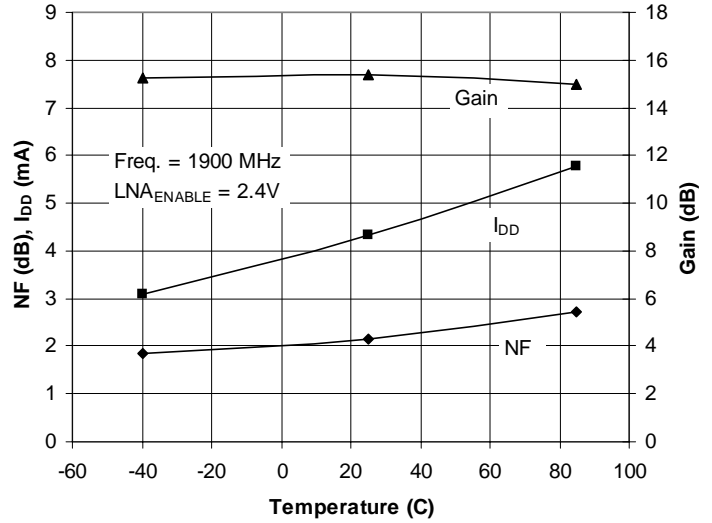
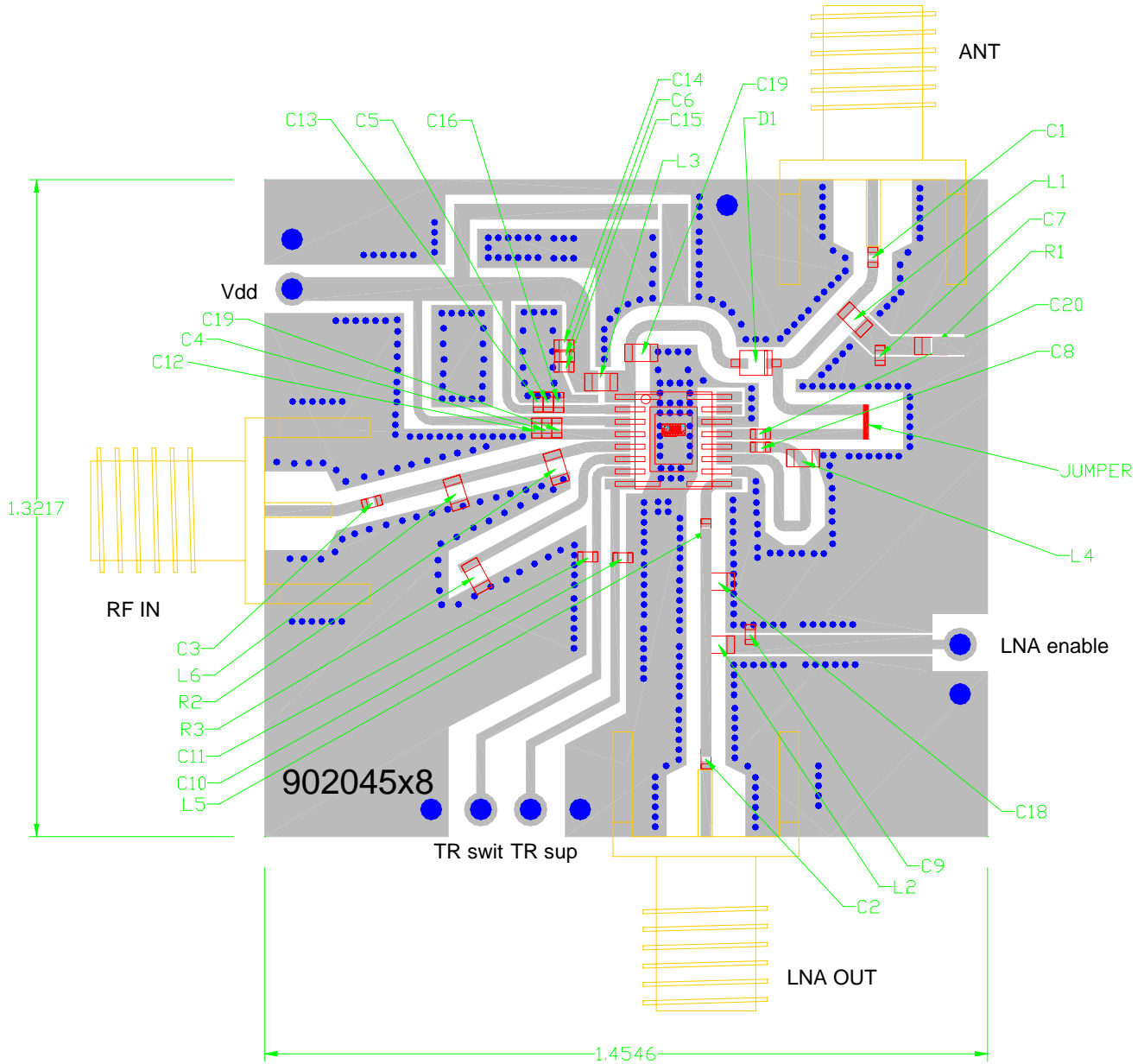


Figure 6. Noise figure, gain and supply current vs. temperature

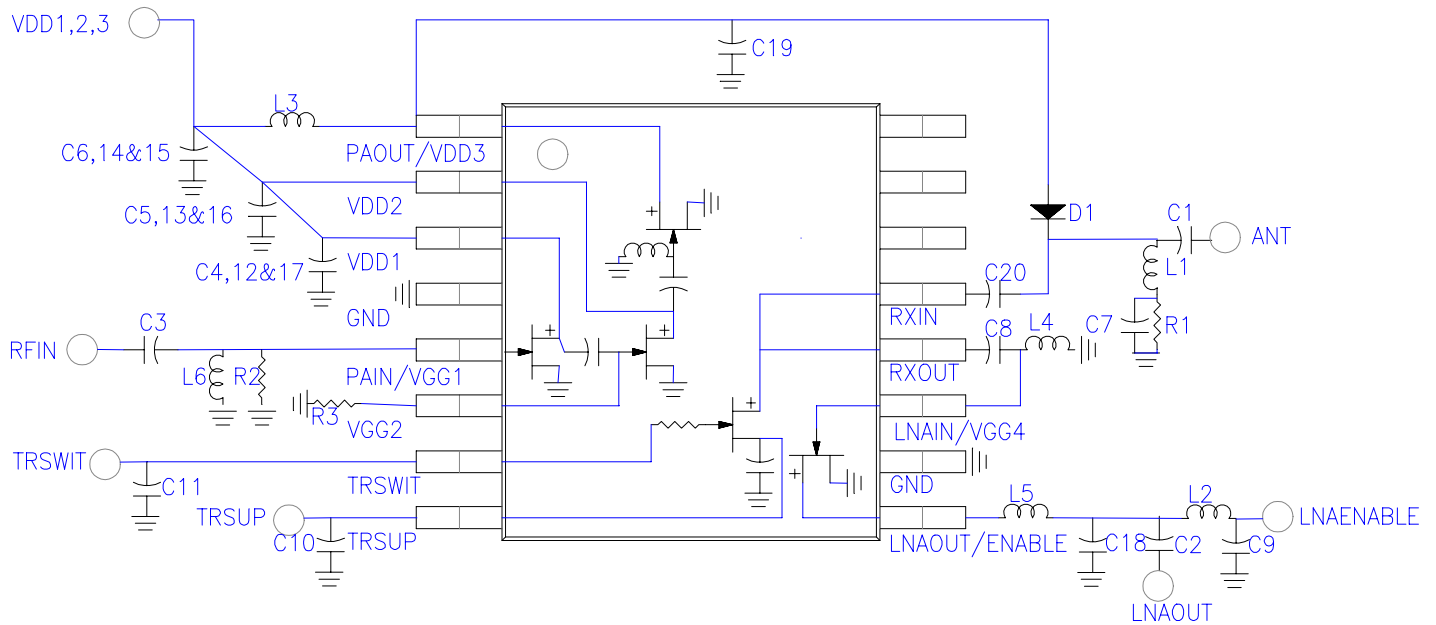


**APPLICATION INFORMATION**



**Figure 7. Component layout and printed circuit drawing for evaluation board.**

**APPLICATION INFORMATION (CONT)**



**Figure 8. Evaluation Board Schematic**

**External components:**

- C1 – C11 MuRata 100 pF 0402 GRM36C0G101J50
- C12 – C14 MuRata 0.1  $\mu$ F 0402 GRM36Y5V104Z1
- C15 – C17 MuRata 33 pF 0402 GRM36C0G330J50
- C18 Dielectric Labs 2.2 pF 0603 C06CF2R2B5UL
- C19 Dielectric Labs 2.4 pF 0603 C06CF2R4B5UL
- C20 MuRata 22 pF 0402 GRM36C0G220G50
- L1 – L3 Coilcraft 27 nH 0603 0603CS-27NXJBB
- L4 Toko 3.3 nH 0603 LL1608-F3N3K
- L5 Coilcraft 7.5 nH 0402 0402CS-7N5XJB
- L6 Toko 2.7 nH 0805 LL2012-F2N7S
- R1 – R2 Panasonic 301 $\Omega$  0603 ERJ-3EKF3010
- R3 Panasonic 10  $\Omega$  0603 ERJ-3EKF10R0V
- D1 Siemens Pin Diode BAR6303W

## GaAsTEK TEST SET UPS

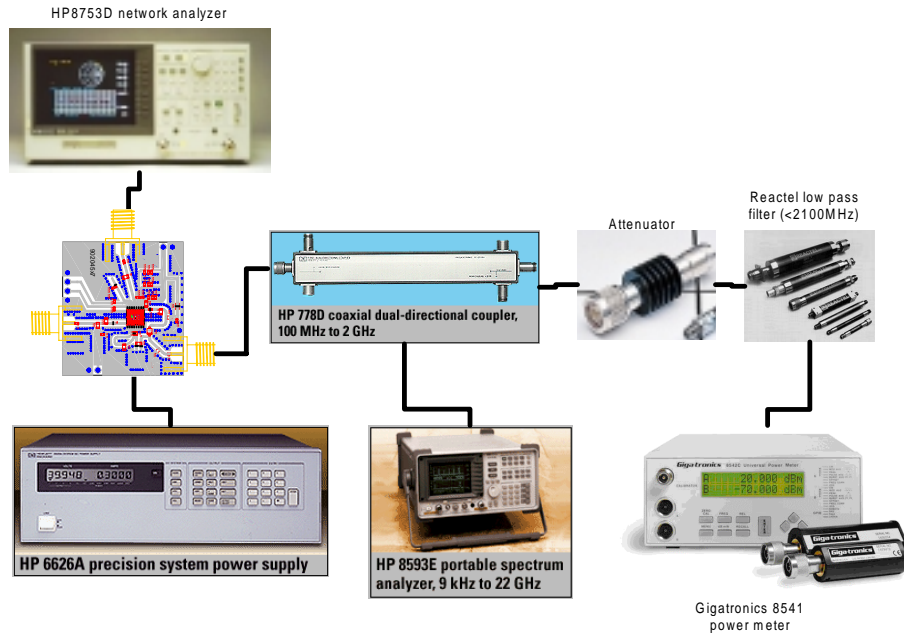


Figure 9. Transmit path power, current, and spurious.

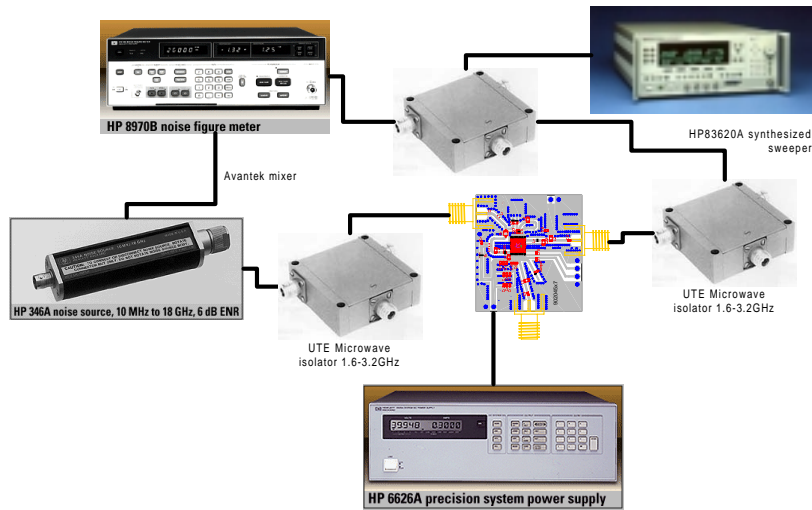


Figure 10. Receive path noise figure and gain.